

Silicon NPN Power Transistors

2SC2615

DESCRIPTION

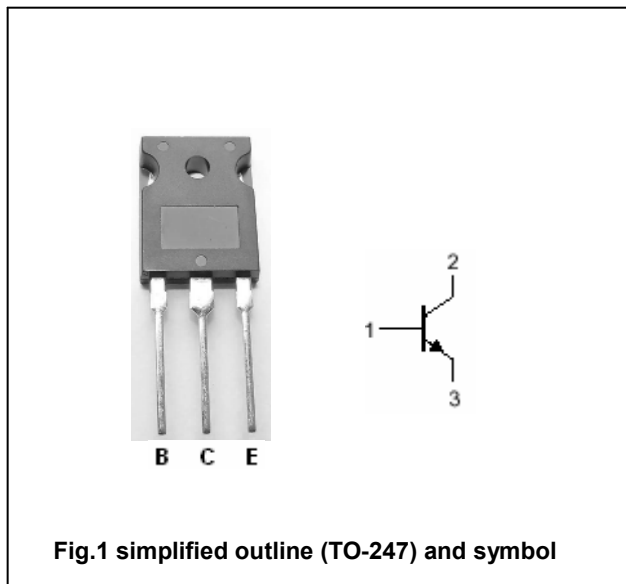
- With TO-247 package
- High voltage,high speed

APPLICATIONS

- For high voltage,high speed and high power switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_c=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	500	V
V_{CEO}	Collector-emitter voltage	Open base	400	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current (DC)		8	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	80	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-emitter sustaining voltage	$I_C=0.2A; I_B=0$	400			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=10mA; I_C=0$	7			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=4A; I_B=0.8A$			1.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=4A; I_B=0.8A$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=400V; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=5V; I_C=0$			0.1	mA
h_{FE-1}	DC current gain	$I_C=4A; V_{CE}=5V$	15			
h_{FE-2}	DC current gain	$I_C=8A; V_{CE}=5V$	7			

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PACKAGE OUTLINE

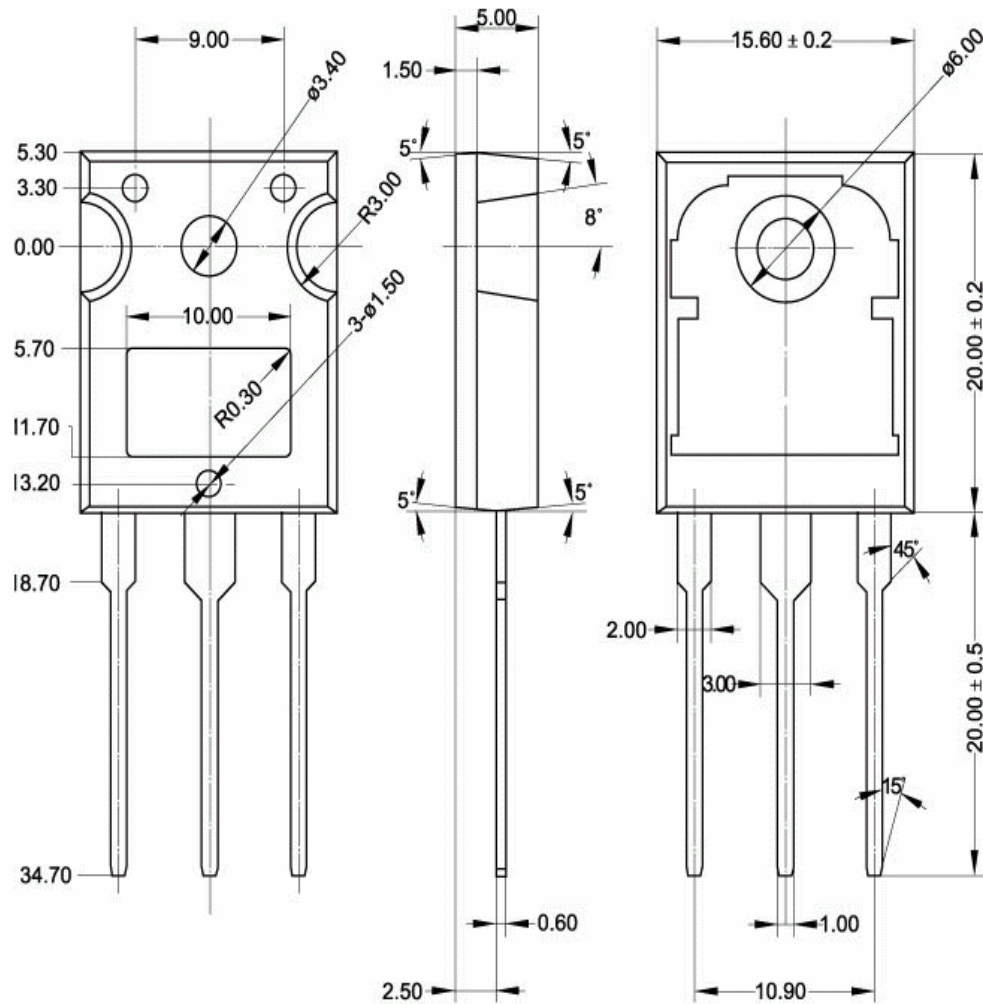


Fig.2 Outline dimensions